

REMARKS

Claims 1-21 were previously pending in this patent application. Claims 20-21 were previously withdrawn in response to a restriction and election requirement under 35 U.S.C. Section 121. Claims 1, 2, 9, and 10 stand rejected, Claims 3-8 are objected to. Further, Claims 11-19 are allowable. Herein, Claims 1 and 9 have been amended. Accordingly, after this Amendment and Response, Claims 1-19 remain pending in this patent application. Further examination and reconsideration in view of the arguments set forth below is respectfully requested.

35 U.S.C. Section 102(b) Rejections

Claims 1, 2, 9, and 10 stand rejected under 35 U.S.C. 102(b) as being anticipated by Applicants' admitted prior art (Figures 1A-1F). These rejections are respectfully traversed.

Independent Claim 1 recites:

A method of fabricating a semiconductor device having a triple LDD (lateral diffused dopants) structure, comprising:

forming a gate structure on a surface of a semiconductor substrate, wherein said gate structure includes a first vertical surface and a second vertical surface;

forming a first spacer adjacent to said first vertical surface and a second spacer adjacent to said second vertical surface, wherein said first spacer has a first thickness and a second thickness that is greater than said first thickness and that abuts said first vertical surface, and wherein said second spacer has a third thickness and a fourth thickness that is greater than said third thickness and that abuts said second vertical surface; and

performing a single implant process to form said triple LDD structure for a drain and a source of said semiconductor device in said semiconductor substrate. (emphasis added)

It is respectfully asserted that the admitted prior art does not disclose the present invention as recited in Independent Claim 1. In particular, the admitted prior art is directed to a method of fabrication in which a first implant process (Figure 1A), a

second implant process (Figure 1C), and a third implant process (Figure 1E) are performed. The admitted prior art fails to disclose a method of fabrication in which a single implant process is performed.

Unlike the admitted prior art, Independent Claim 1 is directed to a method of fabricating a semiconductor device having a triple LDD (lateral diffused dopants) structure. The method includes performing a single implant process to form the triple LDD structure for a drain and a source of the semiconductor device in the semiconductor substrate. While the admitted prior art is directed to performing at least three separate implant processes, Independent Claim 1 is directed to performing a single implant process. Therefore, it is respectfully submitted that Independent Claim 1 is not anticipated by the admitted prior art and is in condition for allowance.

Dependent Claims 2, 9 and 10 are dependent on allowable Independent Claim 1, which is allowable over the admitted prior art. Hence, it is respectfully submitted that Dependent Claims 2, 9, and 10 are patentable over the admitted prior art for the reasons discussed above.

Claim Objections

Claims 3-8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Dependent Claims 3-8 are dependent on allowable Independent Claim 1, which is allowable over the admitted prior art. Hence, it is respectfully submitted that

Dependent Claims 3-8 are patentable over the admitted prior art for the reasons discussed above.

CONCLUSION

It is respectfully submitted that the above arguments and remarks overcome all rejections. For at least the above-presented reasons, it is respectfully submitted that all remaining claims (Claims 1-19) are now in condition for allowance.

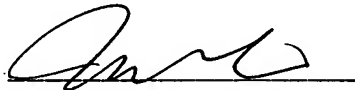
The Examiner is urged to contact Applicants' undersigned representative if the Examiner believes such action would expedite resolution of the present Application.

Please charge any additional fees or apply any credits to our PTO deposit account number: 23-0085.

Respectfully submitted,

WAGNER, MURABITO & HAO, LLP

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James P. Hao
Registration No. 36,398

Two North Market Street, Third Floor
San Jose, CA 95113
(408) 938-9060